# Radiation Damage Effects in the LHCb Vertex Locator (VELO)

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# LHCb Performance

Collecting data at a very good rate:

- Current performance is 1 pb<sup>-1</sup> per hour (at LHCb)

- All of 2010 data can be collected in only a few days

- Progressing well towards year's target of 1 fb<sup>-1</sup>

-In 2010 LHCb same luminosity as ATLAS & CMS

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-Approx. 3x10^{12} n_{eq} p/cm^2
on sensors nearest the PV
(at R = 0.7 cm)
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Already producing an array of impressive results! A couple of examples: BR limit for  $B_s \rightarrow \mu^+ \mu^-$  (<5.6x10<sup>-8</sup>) competitive limit (using 37 pb<sup>-1</sup> vs CDF 3.7 fb<sup>-1</sup>)  $B_s \rightarrow K^+K^-$  lifetime 1.440 ps <u>+</u> 0.096 (stat) <u>+</u> 0.010 (syst) (vs CDF <u>+</u> 0.18)



- •2 Halves (A&C side)
- •21 modules/half
- •R & Phi sensors/module
- •Closed as soon as we reach stable beams.
- •Require at least 6 hits (3 each R&Phi) to reconstruct tracks





VELO fully closed (stable beam)



## **VELO** Facts

- It is the closest detector of the main experiments at LHC to the beam, closes to 8mm
- Most modules are n-on-n
  - Two n-on-p prototypes
- Nominal peak radiation damage is about 1.3x10<sup>14</sup> n<sub>eq</sub> p/cm<sup>2</sup>/2 fb<sup>-1</sup> at R=0.7 cm (from 2001 prediction)

## **VELO** Performance



# **Monitoring Radiation Damage**

- We have four methods of monitoring the radiation damage:
- IV Scans
  - done weekly
  - no measure of depletion voltage (but can trend the current)
- Temperature dependent current measurement
  - done before and after long shutdown
  - do an IV scan at room temperature (significantly larger bulk current, see later)
- Charge collection efficiency (CCE)
  - every ~6 months
  - effective depletion voltage
- Noise vs voltage scan
  - done monthly, gives us another effective depletion voltage
- Due to geometry, we have different bands of radiation damage
  - innermost highest damage, outermost least

## **Radiation Damage Expectation**

The radiation damage in the VELO is modeled by:

Nr<sup>-power</sup>

 $N = n_{eq}/cm^2/2fb^{-1}at 0.8cm$  (diagram b) power = radial dependence

We get non-uniform radiation damage, N can vary by a factor 2 and power ranges from 1.6 to 2.1

Please note this is from 2001 predictions



#### IV Scan

# IV Scan



An example of a ramp up/ramp down cycle on a particular sensor.

We trend the 150V point as a function of time to see how the current changes with luminosity, annealing, and other affects.

IV scans taken weekly. Currently approx 50-70 pb<sup>-1</sup> between them Approx lumi granularity =  $7.5 \times 10^{12} n_{eq}/cm^2$  (for peak r=0.7 cm). Only requires 20-30 minutes, so done between fills

![](_page_9_Figure_5.jpeg)

# **IV** Trending

- For example, VL03AT (non-n sensor, near primary vertex)
- Superimpose luminosity, clear trend in current (measure ΔI = 2.2 μA per 100 pb<sup>-1</sup>).
- Can do a comparative calculation for the n-on-p sensor (see following slide)

![](_page_10_Figure_4.jpeg)

## P-type sensor

- The same plot for the p-type sensor
- Same features (eg winter annealing)
- Measured  $\Delta I = 2.5 \ \mu A \ per \ 100 \ pb^{-1}$ 
  - Very close agreement to previous value!
- Close to PV

![](_page_11_Figure_6.jpeg)

# **High Current Sensors**

- Some sensors have very high initial currents
- These have been normalizing over time (as a function of radiation damage)
- All plateaued now and we expect them to increase in next few hundred pb<sup>-1</sup>.

![](_page_12_Figure_4.jpeg)

## **IV Summary**

Summarize all the currents with luminosity

The clear recent trend of current with the large increase in luminosity delivered is apparent, especially in the most recent data points.

Negative  $\Delta I$  sensors are the high current sensors, they have all plateaued we expect to see increases over next few weeks

![](_page_13_Figure_4.jpeg)

#### Surface vs Bulk currents

![](_page_14_Figure_1.jpeg)

We can separate sensors by how their currents evolve with temperature

# Temperature dependent Current measurement

## IT scan Introduction

- Take IV scan at room temperature
  - We have a warm IV scan previously taken in June
     09 (no radiation damage) so any relative changes
     should arise entirely from irradiation
  - See previous plots from IV scan section

# IT Scan pt II

- We expect the bulk current to anneal significantly over the winter shutdown (approx 40 days of room temperature).
- $\alpha = ~7$  dropping to  $\alpha = ~3.5$
- Expect currents to roughly halve ( a lot of uncertainty in initial position)

![](_page_17_Figure_4.jpeg)

From M. Moll's thesis

#### **IT Scan Results**

Current increases between June 09 and Dec 10 are plotted to give us a measure of the amount arising from radiation damage.

We expect these to roughly halve in the Jan '11 data

Calculate Δ α , ~=200
minutes of pre-annealing
before warm IV scan
Consistent with warming
up detector

![](_page_18_Figure_4.jpeg)

#### Noise vs Voltage Scan

## Noise vs Voltage scan

- Ramp voltage up and take raw data at set points
  - Looking for when noise is 80% of minimum, we call this point 'Effective Minimal Noise Voltage' or EMNV.
  - Taken once a month

![](_page_20_Figure_4.jpeg)

## Noise vs Voltage results I

![](_page_21_Figure_1.jpeg)

As expected, there is a clear trend in the results showing less change in depletion voltage the further out they are. Expect to see these continue to drop as we get closer to type inversion.

#### Latest Results

-Latest results as of
04/07/11
-Zonal bands still
match expectation
-Significant decrease
since previous results

![](_page_22_Figure_2.jpeg)

#### **Charge Collection Efficiency**

## **CCE** Introduction

- Take data for a range of voltages
- Plot these and fit a Landau/Gauss
- Take the MPV and trend it as a f(V)
- Defined 80% of depleted electrons = effective depletion voltage (done to match production)
- Will also be able to see the change in signal number of electrons as the radiation damage gets significantly higher
- Infrequently taken as requires several hours of beam (data can't be used for physics)

![](_page_24_Figure_7.jpeg)

## CCE Introduction 2

![](_page_25_Figure_1.jpeg)

On the left, an example of the Landaus at a range of voltages, we take these MPVs and plot them as a function of voltage.

![](_page_25_Figure_3.jpeg)

## **CCE** Results

- We can divide the R sensors into bands
- Compare to 2010 data (no radiation damage) and see how EDV has changed
- Only done for 40 pb<sup>-1</sup> next CCE scan due in next couple of weeks after ~400 pb<sup>-1</sup>

![](_page_26_Figure_4.jpeg)

## Summary

- VELO has clear radiation damage effects
  - A number of measures of keeping track of these, including a novel way of looking at depletion voltage without affecting data taking ability
  - Sensors with bulk defects are normalizing as expected
  - Interesting annealing affects are being observed too
  - Next few months will have confirmation on data of the radiation model, damage observed vs predicted, etc

### **Future Expectations**

- We expect to see the depletion voltage to minimize soon, and type inversion
  - Taking a CCE scan very shortly to analyze for this
    - Fortunately with different bands of R we don't need to be exactly at the right luminosity to see the type inversion
- Another warm IV scan over winter shutdown 2011 to anneal currents further

#### **BACKUP SLIDES**

## Backup – CCE Track Selection

- Look for 'golden tracks' we voltage step one in every five sensors whilst holding the neighbouring sensors at operational voltage
- Allows us to use tracking information to look for sensors

![](_page_30_Figure_3.jpeg)

#### IV Backup – Surface Damaged Sensor

- One anomalous sensor that has massive current increase with luminosity
- Approximately 6 μA per 100 pb<sup>-1</sup>!
- Surface oxide charge saturation theory

![](_page_31_Figure_4.jpeg)

Four days with no beam, surface oxide discharged

## Backup – Two bands of DV

- There are two groups of sensors w.r.t DV in the VELO
  - One band around 30-40 V
  - Another band at 50-60 V

#### Backup - Noise vs Voltage for p-type

 EDV very different vs n-type (deplete from different side of sensor – n-type will minimize noise before DV)

Sensor	Initial EDV (V)	40 pb <sup>-1</sup> EDV (V)	ΔEDV (f/i)
P-type	10	8.4	0.84
Close n-type	50	52.8	1.06

# Backup - CCE Results for p-type

- P-type
  - Nominal production DV = 100V
  - CCE results = 70 V

R band(mm)	P-type sensor (ΔEDV) (V)	Mean (ΔEDV) (V)	Nominal n-type (ΔEDV)
11-16	-9	-3.2	-2
16-23	-1	-1.8	N/A
23-34	-2	-1	-1
34-45	-1	0	0

Higher production EDV than other sensors
 – Rate at which it is falling is higher too